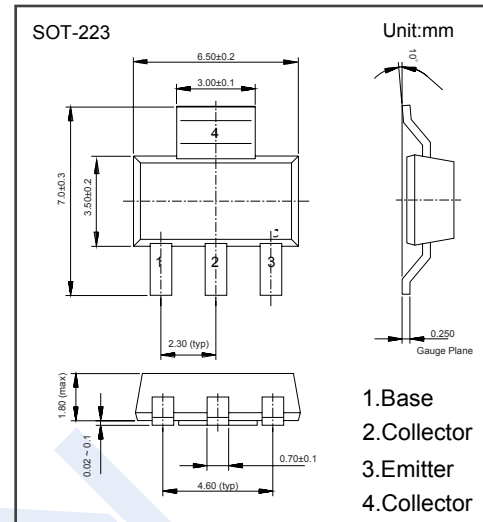


PNP Transistors

CZT2955 (KZT2955)

■ Features

- High Current
- Low Voltage
- Surface Mounted Power Amplifier Application
- Complement to CZT3055

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-100	V
Collector - Emitter Voltage	V_{CE0}	-60	
Emitter - Base Voltage	V_{EB0}	-7	
Collector Current - Continuous	I_C	-6	A
Collector Power Dissipation	P_C	1	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -1\text{mA}$, $I_E = 0$	-100			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -30\text{mA}$, $I_B = 0$	-60			
		$I_C = -30\text{mA}$, $I_B = 0$, $R_{BE} = 100\Omega$	-70			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -1\text{mA}$, $I_C = 0$	-7			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -100\text{V}$, $I_B = 0$			-100	μA
Collector cut-off current	I_{CE0}	$V_{CE} = -30\text{V}$, $I_E = 0$			-700	μA
	I_{CEV}	$V_{CE} = -100\text{V}$, $V_{EB} = 1.5\text{V}$			-1	mA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5\text{V}$, $I_C = 0$			-5	mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4\text{A}$, $I_B = -400\text{mA}$			-1.1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -4\text{A}$, $I_B = -400\text{mA}$			-1.2	
Base-emitter voltage	V_{BE}	$V_{CE} = -44\text{V}$, $I_C = -4\text{A}$			-1.5	
DC current gain	$h_{FE(1)}$	$V_{CE} = -4\text{V}$, $I_C = -4\text{A}$	20		70	
	$h_{FE(2)}$	$V_{CE} = -4\text{V}$, $I_C = -6\text{A}$	5			
Transition frequency	f_T	$V_{CE} = -10\text{V}$, $I_C = -500\text{mA}$, $f = 1\text{MHz}$	2.5			MHz